

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

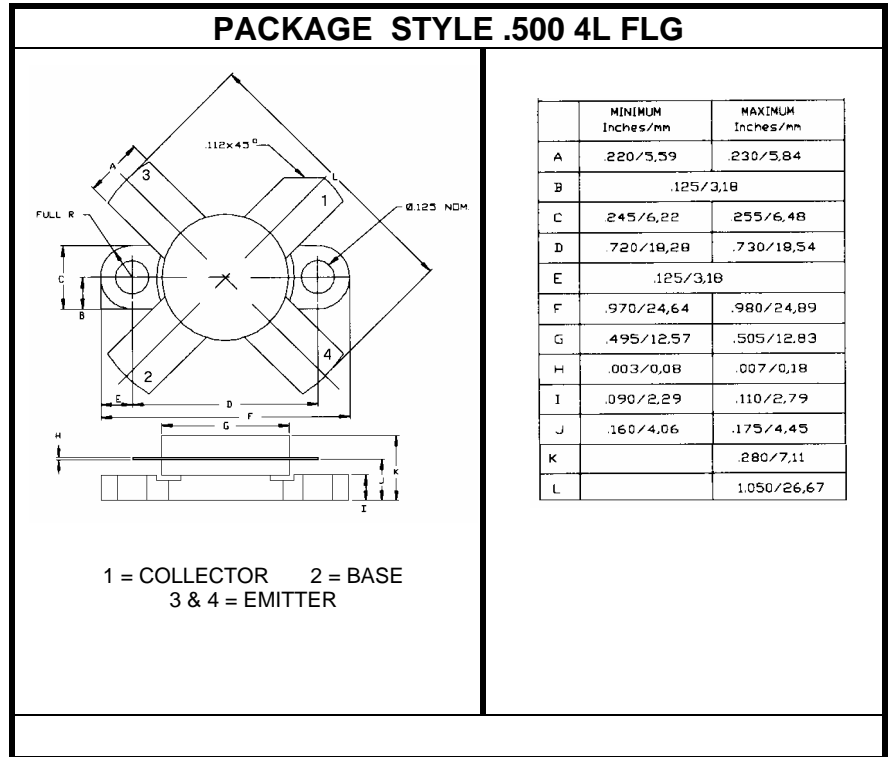
The **ASI BLW77** is Designed for use in class-AB or class-B operated high power transmitters in the H.F. and V.H.F bands and, as a Linear amplifier in the H.F. band.

FEATURES:

- $P_G = 12$ dB min. at 15-30 W/1.6-28 MHz
- Common Emitter
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CB}	70 V
V_{CE}	35 V
P_{DISS}	245 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.71 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	35			V
BV_{CES}	$I_C = 50$ mA	70			V
BV_{EBO}	$I_E = 20$ mA	3.0			V
I_{CES}	$V_E = 35$ V			20	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 7.0$ A	15		80	---
C_c	$V_{CB} = 28$ V $f = 1.0$ MHz		225		pF
G_p	$V_{CE} = 28$ V $I_{C(ZS)} = 0.1$ A $f = 1.6-28$ MHz $P_L = 15-130$ W (PEP)	12			dB
d_3				-30	dB
η			37.5		